



**(19) World Intellectual Property Organization
International Bureau**

**(43) International Publication Date
26 May 2005 (26.05.2005)**

PCT

(10) International Publication Number
WO 2005/048351 A1

(51) International Patent Classification⁷: H01L 29/10,
29/739, 21/331

Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(21) International Application Number: PCT/CH2004/000691

(84) **Designated States** (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

(22) International Filing Date: 16 November 2004 (16.11.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data: 03405816.4 17 November 2003 (17.11.2003) EP

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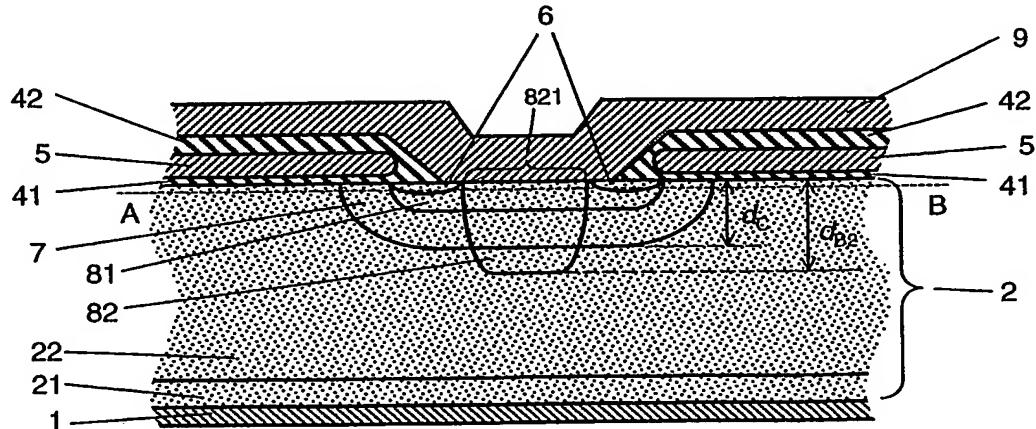
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Published:

- with international search report
- with amended claims

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: IGBT CATHODE DESIGN WITH IMPROVED SAFE OPERATING AREA CAPABILITY



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(57) Abstract: In an insulated gate bipolar transistor, an improved safe operating area capability is achieved according to the invention by a two-fold base region comprising a first base region (81), which is disposed in the channel region (7) so that it encompasses the one or more source regions (6), but does not adjoin the second main surface underneath the gate oxide layer (41), and a second base region (82) is disposed in the semiconductor substrate (2) underneath the base contact area (821) so that it partially overlaps with the channel region (7) and with the first base region (81).